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### FDS6890A

### **Dual N-Channel 2.5V Specified PowerTrench™ MOSFET**

### **General Description**

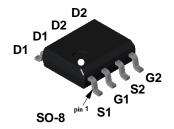
These N-Channel 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

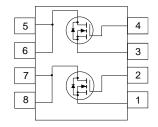
### **Applications**

- DC/DC converter
- Motor drives

### **Features**

- 7.5 A, 20 V.  $R_{DS(ON)} = 0.018~\Omega~$  @  $V_{GS} = 4.5~V$   $R_{DS(ON)} = 0.022~\Omega~$  @  $V_{GS} = 2.5~V.$
- Low gate charge (23nC typical).
- Fast switching speed.
- High performance trench technology for extremely low  $R_{\scriptscriptstyle DS(ON)}$ .
- High power and current handling capability.





### Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		20	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	7.5	А
	- Pulsed		20	
P <sub>D</sub>	Power Dissipation for Dual Operation		2.0	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1.0	
		(Note 1c)	0.9	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta}JA$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R <sub>e</sub> JC	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W
			90	

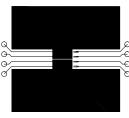
**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS6890A FDS6890A		13	12mm 25	

Symbol	Parameter	Test Conditions		Тур	Max	Units
Off Char	acteristics					!
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		14		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 8 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 0 V			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.5	0.8	1.5	V
ΔV <sub>GS(th)</sub> ΔT <sub>J</sub>	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , Referenced to $25^{\circ}C$		-3.5		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 2.5 \text{ V}, I_D = 6.5 \text{ A}$		0.013 0.021 0.016	0.018 0.034 0.022	Ω
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 2.0 \text{ V}, V_{DS} = 5 \text{ V}$				Α
<b>g</b> FS	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 7.5 A		35		S
Dvnamio	Characteristics		•		•	•
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		2130		pF
Coss	Output Capacitance	f = 1.0 MHz		545		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			270		pF
Switchir	ng Characteristics (Note 2)		-			
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$		13	24	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		26	42	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	1		65	90	ns
t <sub>f</sub>	Turn-Off Fall Time	1		23	37	ns
Q <sub>g</sub>	Total Gate Charge	$V_{DS} = 10 \text{ V}, I_D = 7.5 \text{ A},$		23	32	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 4.5 V$ ,		3.2		nC
Q <sub>gd</sub>	Gate-Drain Charge	7		4.4		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings			-	
I <sub>S</sub>	Maximum Continuous Drain-Source				1.3	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.3 A (Note 2)		0.65	1.2	V
	_			_		

#### Notes:

 $\textbf{1.} \ \ \mathsf{R}_{\theta\mathsf{JA}} \ \mathsf{is} \ \mathsf{the} \ \mathsf{sum} \ \mathsf{of} \ \mathsf{the} \ \mathsf{junction} \mathsf{-to} \mathsf{-case} \ \mathsf{and} \ \mathsf{case} \mathsf{-to} \mathsf{-ambient} \ \mathsf{thermal} \ \mathsf{resistance} \ \mathsf{where} \ \mathsf{the} \ \mathsf{case} \ \mathsf{thermal} \ \mathsf{reference} \ \mathsf{is} \ \mathsf{defined} \ \mathsf{as} \ \mathsf{the} \ \mathsf{solder} \ \mathsf{mounting}$ surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



Scale 1 : 1 on letter size paper



a) 78° C/W when mounted on a 0.5 in² pad of 2 oz. copper.

b) 125° C/W when mounted on a 0.02 in² pad of 2 oz. copper.

c) 135° C/W when mounted on a mounted on a minimum pad.



### Typical Characteristics (continued)

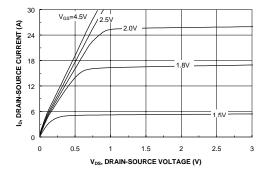


Figure 1. On-Region Characteristics.

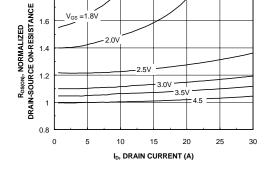


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

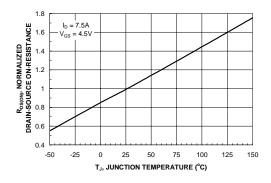


Figure 3. On-Resistance Variation with Temperature.

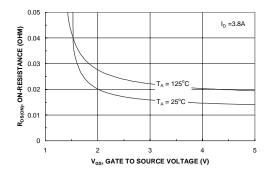


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

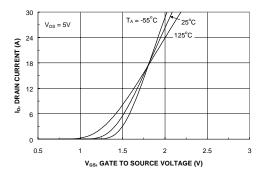


Figure 5. Transfer Characteristics.

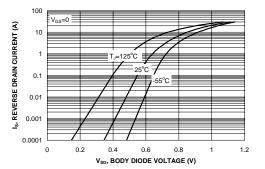
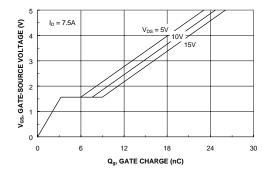


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics (continued)



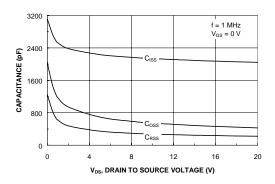
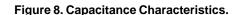
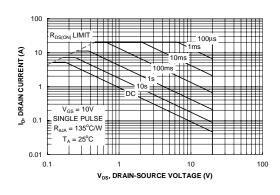


Figure 7. Gate Charge Characteristics.





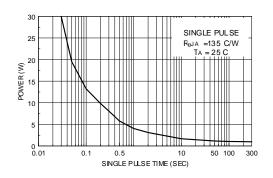


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

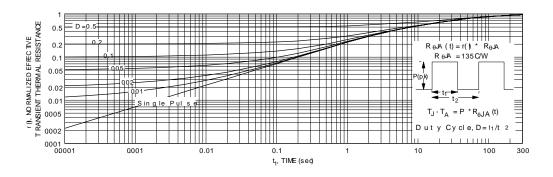


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient themal response will change depending on the circuit board design.

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